TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

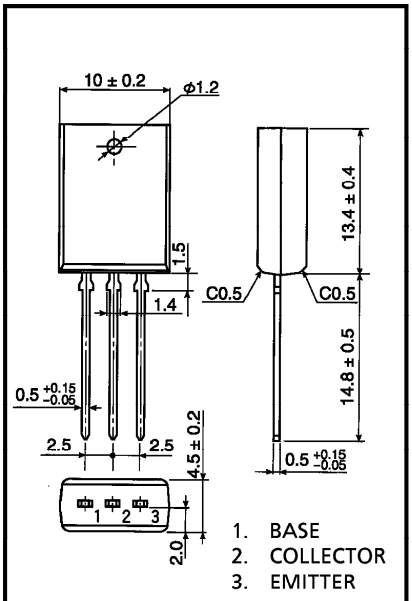
2SD2526

HIGH POWER SWITCHING APPLICATIONS

HAMMER DRIVE, PULSE MOTOR DRIVE APPLICATIONS

- High DC Current Gain : h_{FE} = 2000 (Min.) (V_{CE} = 3V, I_C = 3A)
- Low Saturation Voltage : $V_{CE\,(sat)}$ = 1.5V (Max.) (I_C = 3A)
- Complementary to 2SB1641

Unit in mm



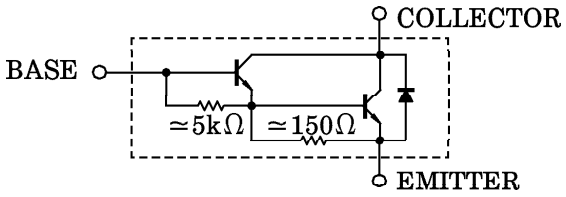
JEDEC	—
EIAJ	—
TOSHIBA	2-10T1A

Weight : 1.5g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	100	V
Collector-Emitter Voltage		V_{CEO}	100	V
Emitter-Base Voltage		V_{EBO}	7	V
Collector Current	DC	I_C	5	A
	Pulse		8	
Base Current		I_B	0.5	A
Collector Power Dissipation		P_C	1.8	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	−55~150	°C

EQUIVALENT CIRCUIT



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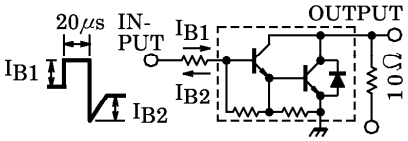
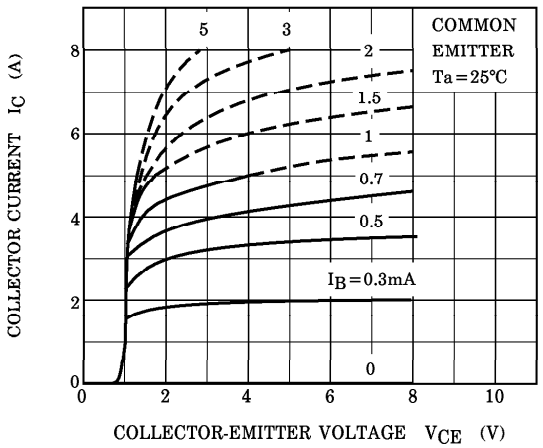
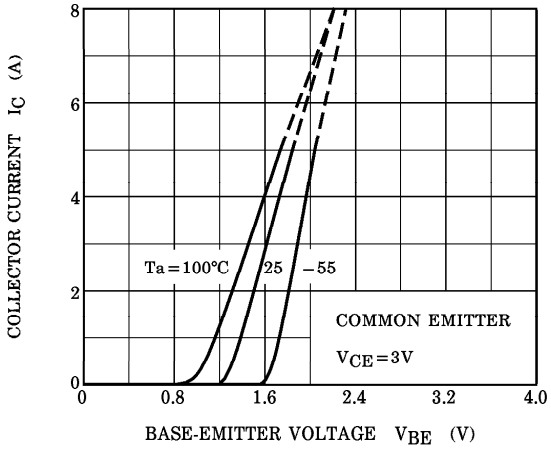
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	V_{CB} = 100V, I_E = 0	—	—	100	μA
Emitter Cut-off Current		I_{EBO}	V_{EB} = 6V, I_C = 0	—	—	2.5	mA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	I_C = 30mA, I_B = 0	100	—	—	V
DC Current Gain		$h_{FE(1)}$	V_{CE} = 3V, I_C = 3A	2000	—	15000	
		$h_{FE(2)}$	V_{CE} = 3V, I_C = 5A	1000	—	—	
Collector-Emitter Saturation Voltage		$V_{CE(sat)(1)}$	I_C = 3A, I_B = 6mA	—	1.1	1.5	V
		$V_{CE(sat)(2)}$	I_C = 5A, I_B = 20mA	—	1.3	2.5	
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	I_C = 3A, I_B = 6mA	—	1.7	2.5	V
Switching Time	Turn-on Time	t_{on}		—	1.0	—	μs
	Storage Time	t_{stg}		—	4.0	—	
	Fall Time	t_f		—	2.5	—	

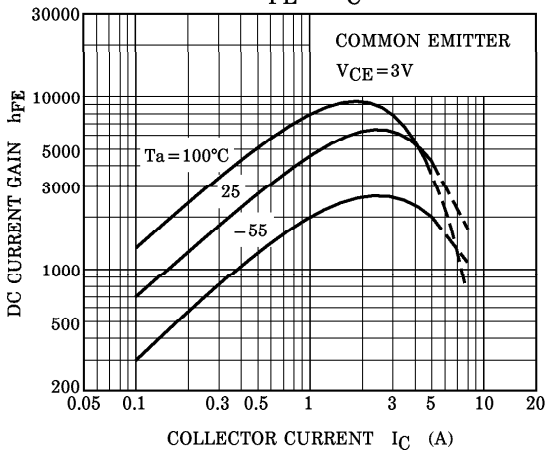
I_C – V_{CE}



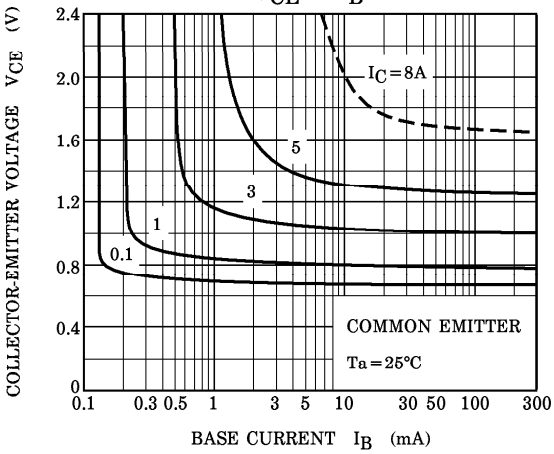
I_C – V_{BE}



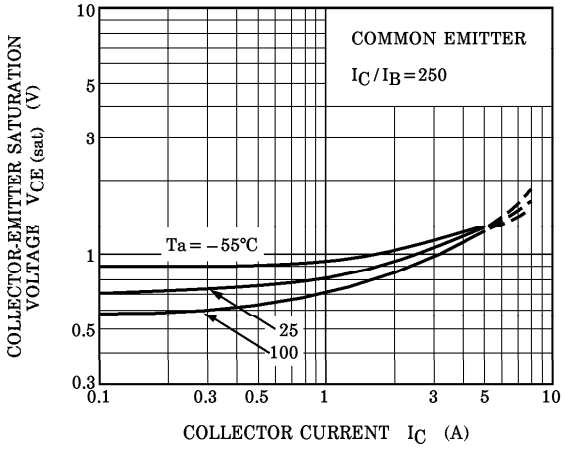
h_{FE} – I_C



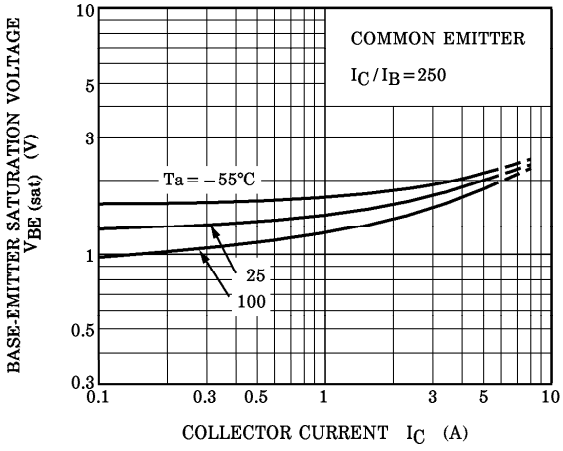
V_{CE} – I_B



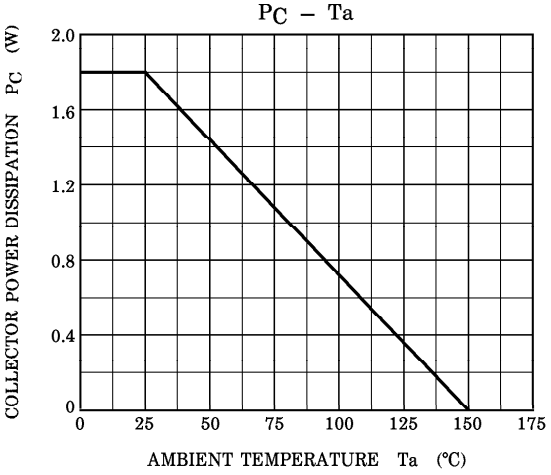
$V_{CE\,(sat)}$ – I_C



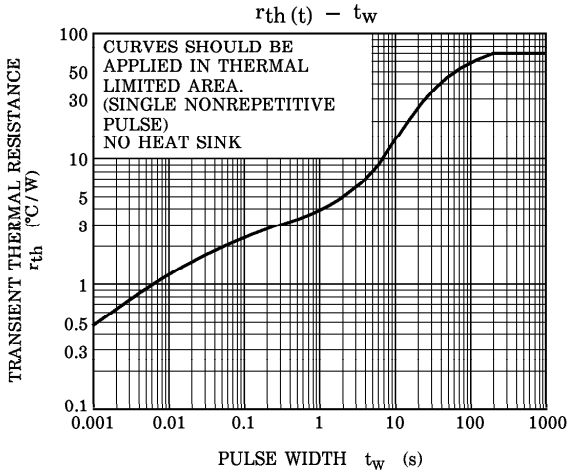
$V_{BE\,(sat)}$ – I_C



P_C – Ta



r_{th} (t) – t_w



SAFE OPERATING AREA